

1N4448WT

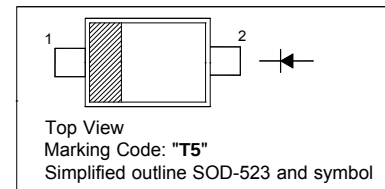
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Silicon Epitaxial Planar Switching Diode

Fast Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

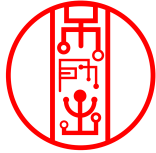


Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	125	mA
Forward Continuous Current	I_{FM}	250	mA
Non-Repetitive Peak Forward Surge Current (at $t = 1\text{ }\mu\text{s}$)	I_{FSM}	0.5	A
Power Dissipation	P_d	150	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	0.62 - - -	0.72 0.855 1 1.25	V
Reverse Leakage Current at $V_R = 80\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$, $T_J = 150\text{ }^{\circ}\text{C}$ at $V_R = 25\text{ V}$, $T_J = 150\text{ }^{\circ}\text{C}$	I_R	- - - -	100 25 50 30	nA nA μA μA
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	80	-	V
Capacitance at $V_R = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	-	4	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	4	ns



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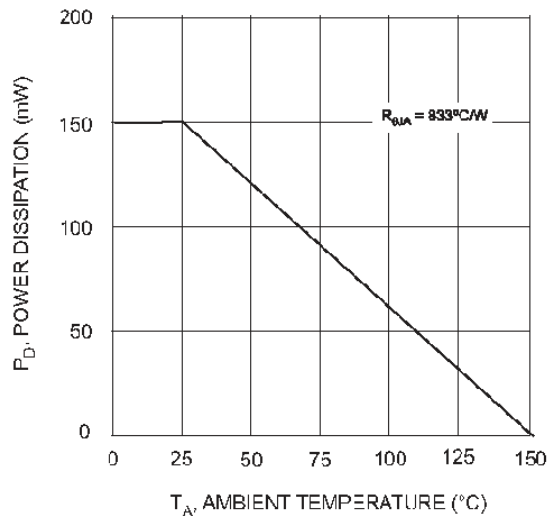


Fig. 1 Derating Curve

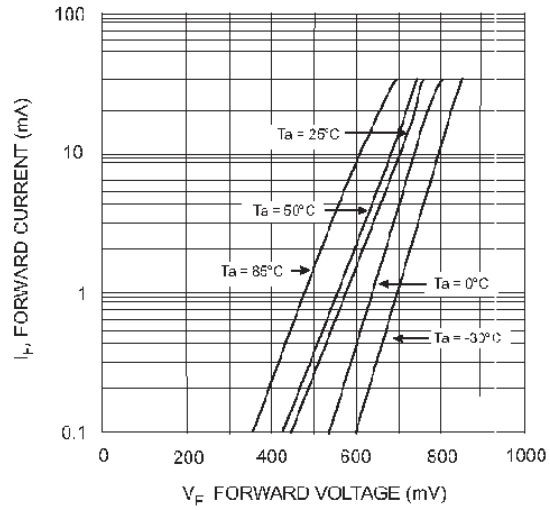


Fig. 2 Typical Forward Characteristics

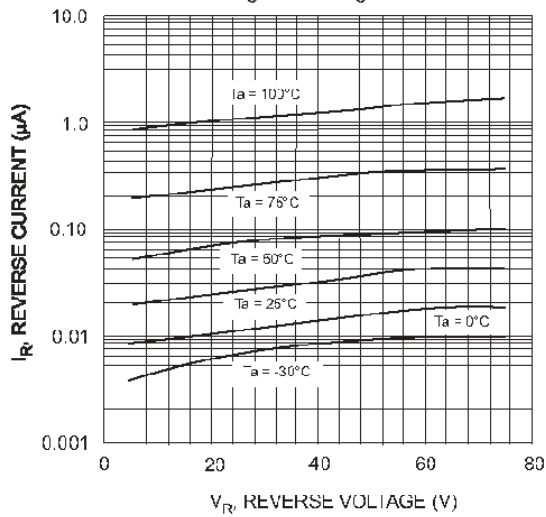


Fig. 3 Typical Reverse Characteristics

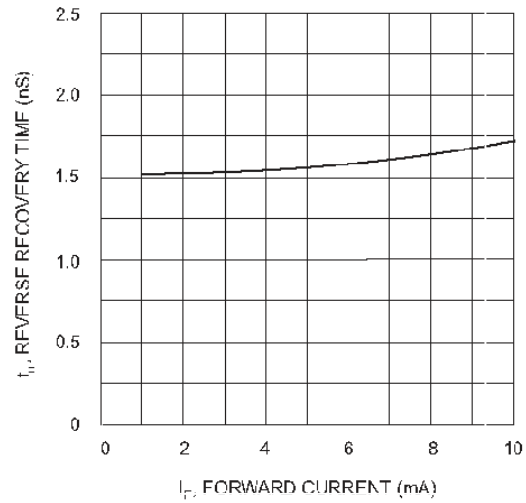
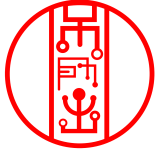


Fig. 4 Reverse Recovery Time vs. Forward Current

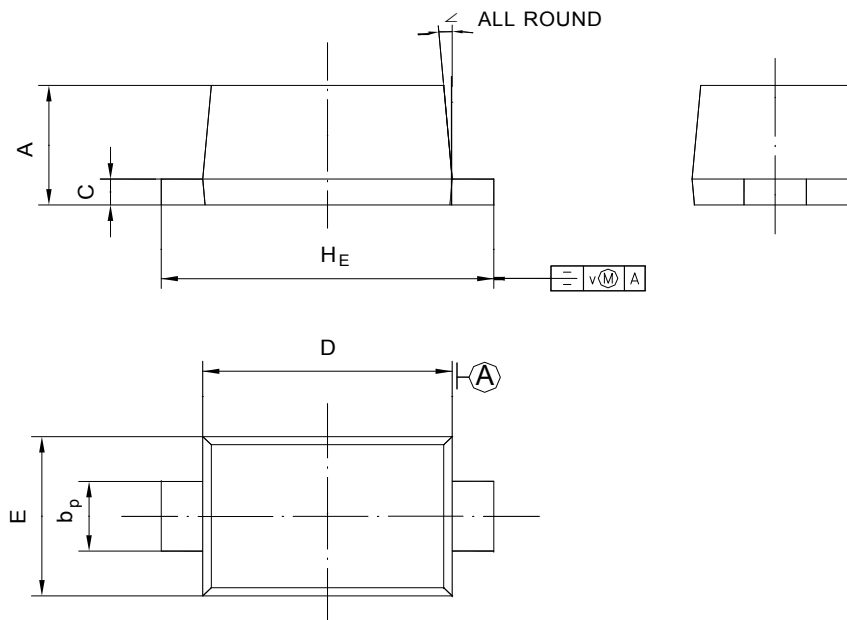


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PACKAGE OUTLINE

SOD-523

Plastic surface mounted package; 2 leads



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°